

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - soldering point (pin 4)	R_{thJS}		-	-	25	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	115	
		6 cm ² cooling area ¹⁾	-	-	70	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=-3\text{ V}, I_D=250\text{ }\mu\text{A}$	240	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=3\text{ V}, I_D=108\text{ }\mu\text{A}$	-2.1	-1.4	-1	
Drain-source cutoff current	$I_{D(off)}$	$V_{DS}=240\text{ V}, V_{GS}=-3\text{ V}, T_j=25\text{ °C}$	-	-	0.1	μA
		$V_{DS}=240\text{ V}, V_{GS}=-3\text{ V}, T_j=125\text{ °C}$	-	-	10	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	10	nA
On-state drain current	I_{DSS}	$V_{GS}=0\text{ V}, V_{DS}=10\text{ V}$	50	-	-	mA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=0\text{ V}, I_D=25\text{ mA}$	-	6.5	20	Ω
		$V_{GS}=10\text{ V}, I_D=0.35\text{ A}$	-	4.2	6.0	
Transconductance	g_{fs}	$ V_{DS} >2 I_D /R_{DS(on)max}, I_D=0.28\text{ A}$	0.18	0.36	-	S

Threshold voltage $V_{GS(th)}$ sorted in bands³⁾

J	$V_{GS(th)}$	$V_{DS}=3\text{ V}, I_D=108\text{ }\mu\text{A}$	-1.2	-	-1	V
K			-1.35	-	-1.15	
L			-1.5	-	-1.3	
M			-1.65	-	-1.45	
N			-1.8	-	-1.6	

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (single layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ Each reel contains transistors out of one band whose identifying letter is printed on the reel label. A specific band cannot be ordered separately.

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Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=-3\text{ V}$, $V_{DS}=25\text{ V}$, $f=1\text{ MHz}$	-	82	108	pF
Output capacitance	C_{oss}		-	12	16	
Reverse transfer capacitance	C_{rss}		-	6	10	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=120\text{ V}$, $V_{GS}=-2\ldots 5\text{ V}$, $I_D=0.2\text{ A}$, $R_G=7.6\ \Omega$	-	4.4	6.6	ns
Rise time	t_r		-	4.1	6.2	
Turn-off delay time	$t_{d(off)}$		-	22	33	
Fall time	t_f		-	35	53	

Gate Charge Characteristics

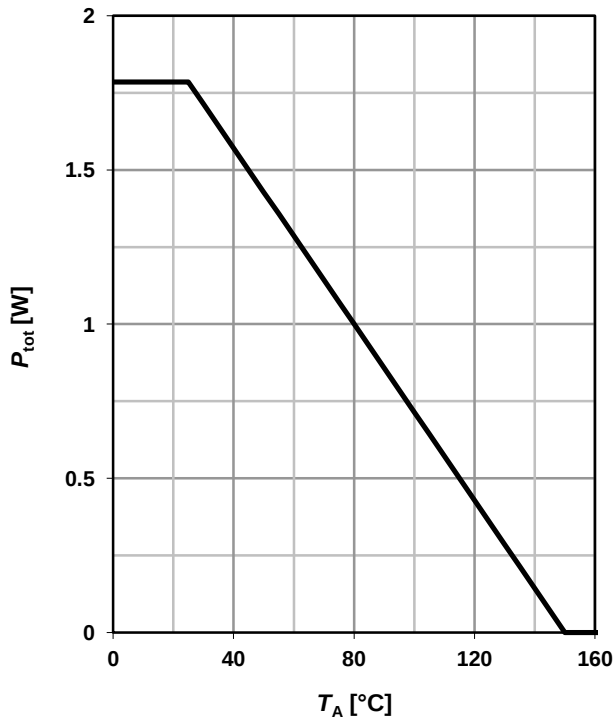
Gate to source charge	Q_{gs}	$V_{DD}=192\text{ V}$, $I_D=0.2\text{ A}$, $V_{GS}=-3\text{ to }5\text{ V}$	-	0.24	0.36	nC
Gate to drain charge	Q_{gd}		-	1.7	2.6	
Gate charge total	Q_g		-	3.8	5.7	
Gate plateau voltage	$V_{plateau}$		-	0.37	-	V

Reverse Diode

Diode continuous forward current	I_S	$T_A=25\text{ °C}$	-	-	0.35	A
Diode pulse current	$I_{S,pulse}$		-	-	1.4	
Diode forward voltage	V_{SD}	$V_{GS}=-3\text{ V}$, $I_F=0.35\text{ A}$, $T_J=25\text{ °C}$	-	0.79	1.2	V
Reverse recovery time	t_{rr}	$V_R=120\text{ V}$, $I_F=0.2\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$	-	53	80	ns
Reverse recovery charge	Q_{rr}		-	65	97	nC

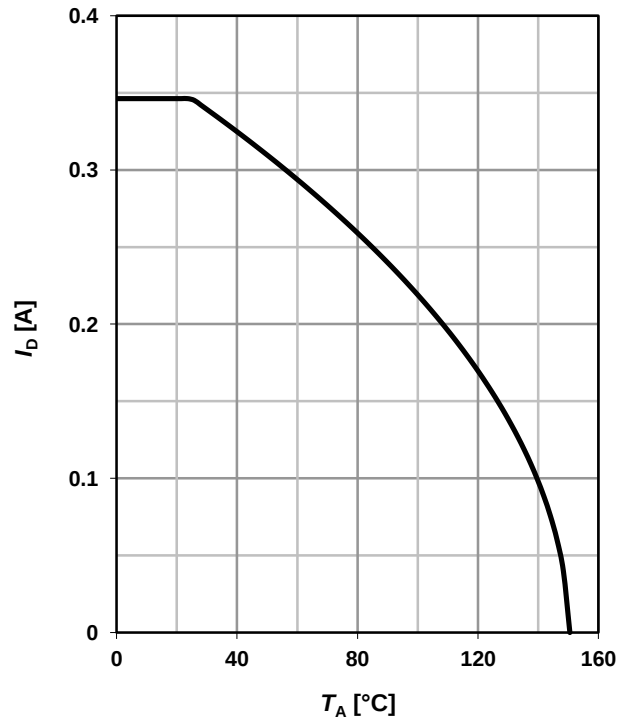
1 Power dissipation

$$P_{\text{tot}} = f(T_A)$$



2 Drain current

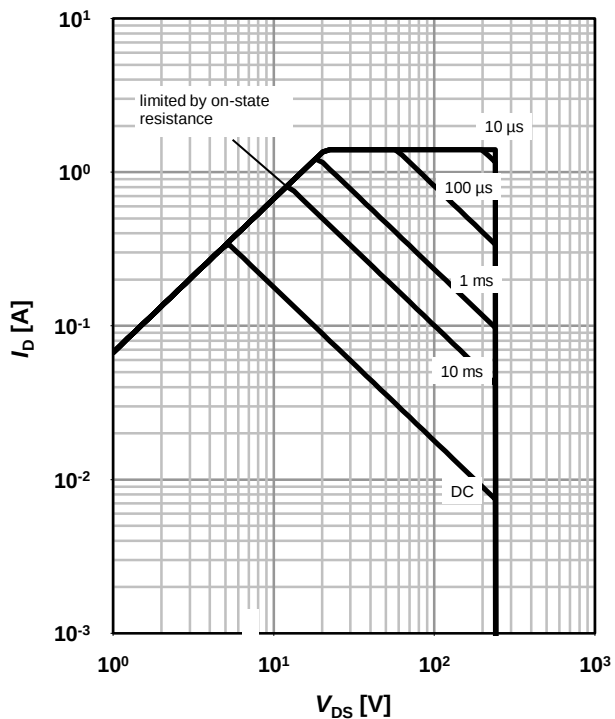
$$I_D = f(T_A); V_{\text{GS}} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_A = 25^{\circ}\text{C}; D = 0$$

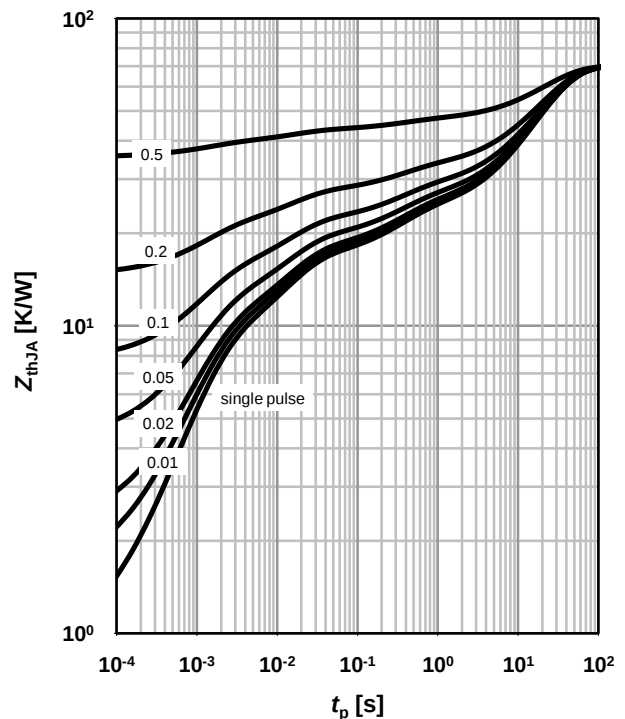
parameter: t_p



4 Max. transient thermal impedance

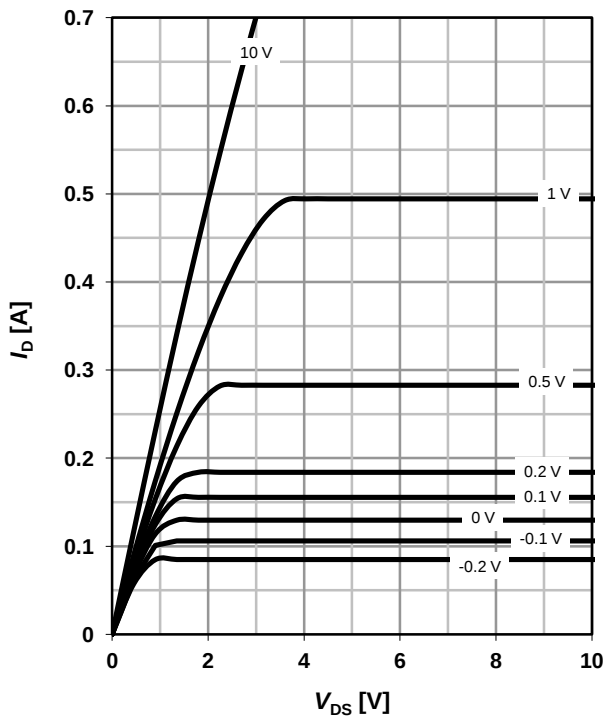
$$Z_{\text{thJA}} = f(t_p)$$

parameter: $D = t_p/T$



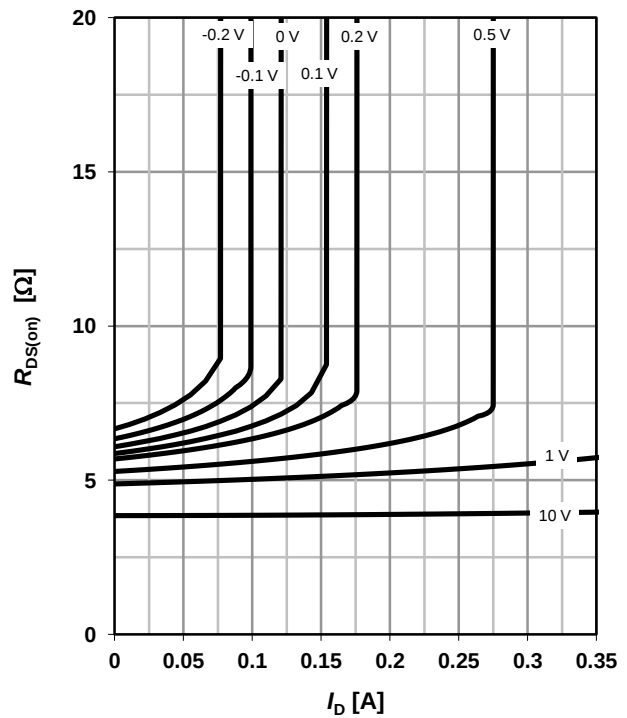
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

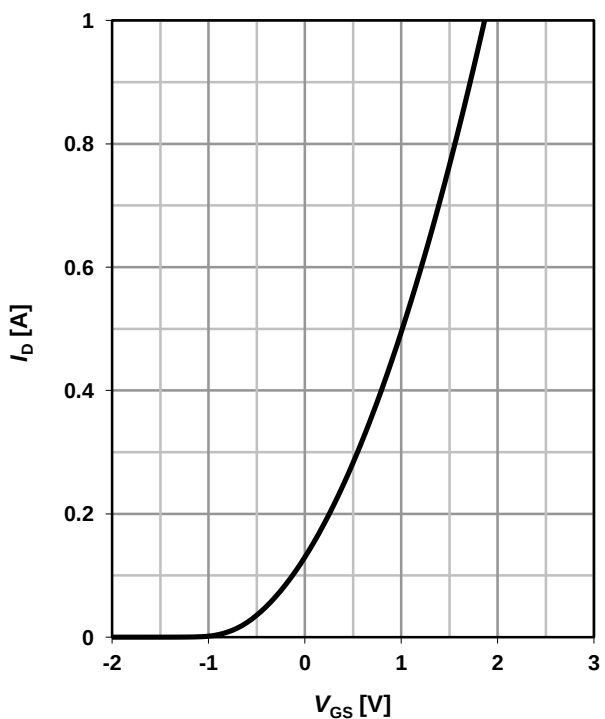
parameter: V_{GS}


6 Typ. drain-source on resistance

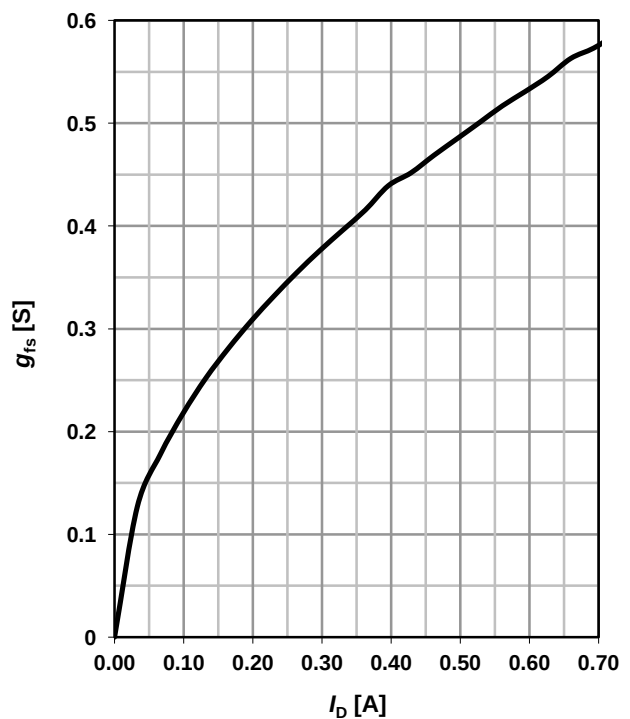
 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

parameter: V_{GS}


7 Typ. transfer characteristics

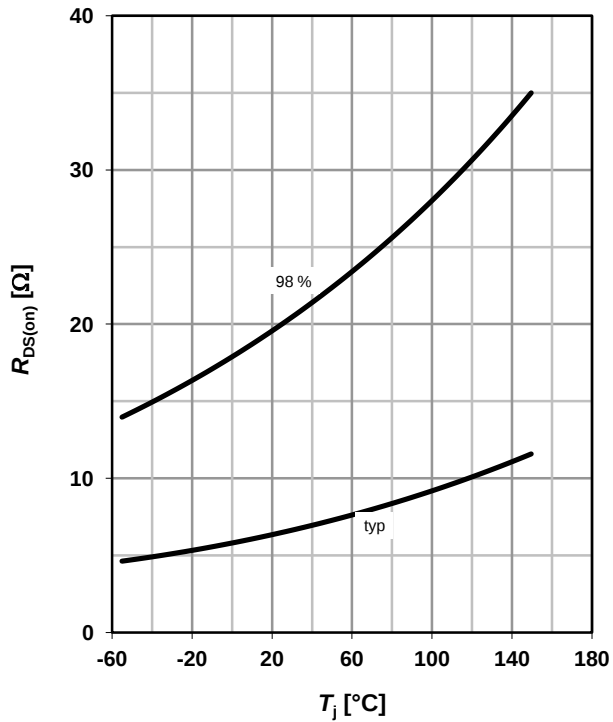
 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$


8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$


9 Drain-source on-state resistance

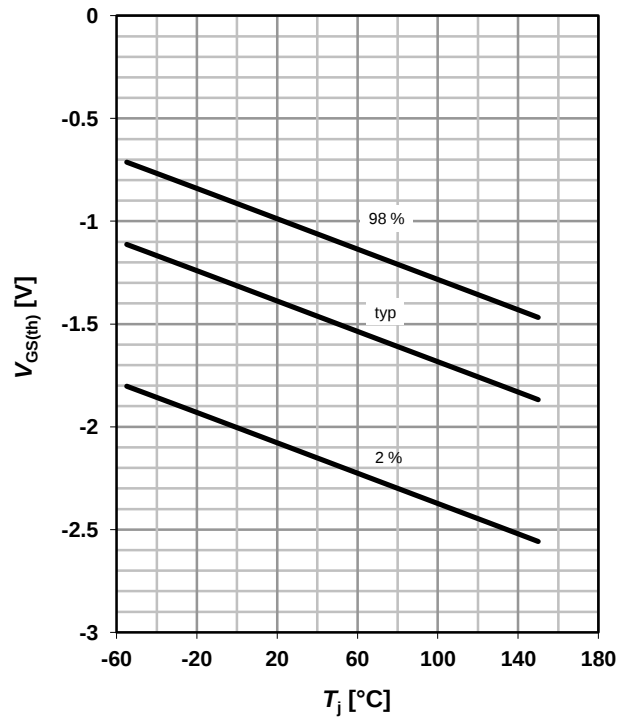
$$R_{DS(on)} = f(T_j); I_D = 0.025 \text{ A}; V_{GS} = 0 \text{ V}$$



10 Typ. gate threshold voltage

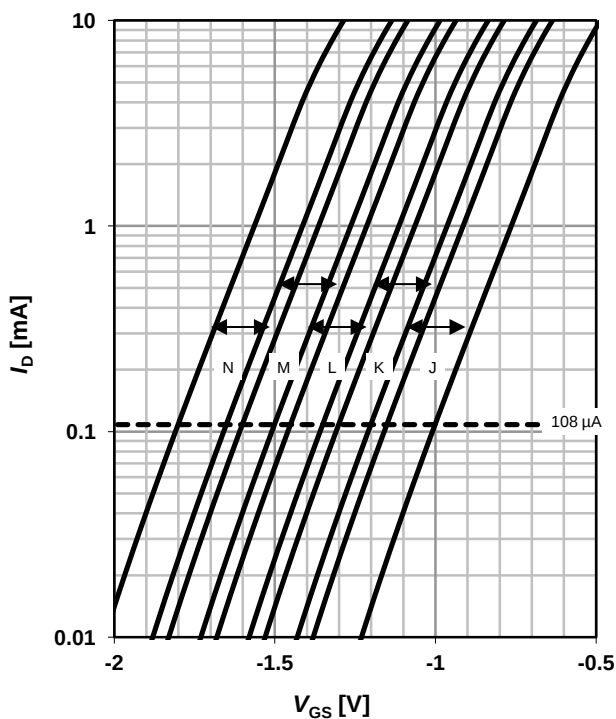
$$V_{GS(th)} = f(T_j); V_{DS} = 3 \text{ V}; I_D = 108 \text{ μA}$$

parameter: I_D



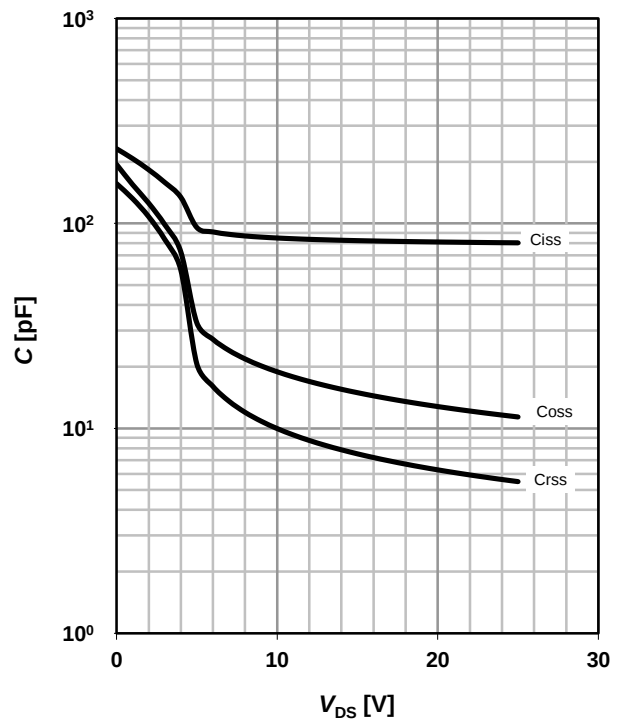
11 Threshold voltage bands

$$I_D = f(V_{GS}); V_{DS} = 3 \text{ V}; T_j = 25 \text{ °C}$$



12 Typ. capacitances

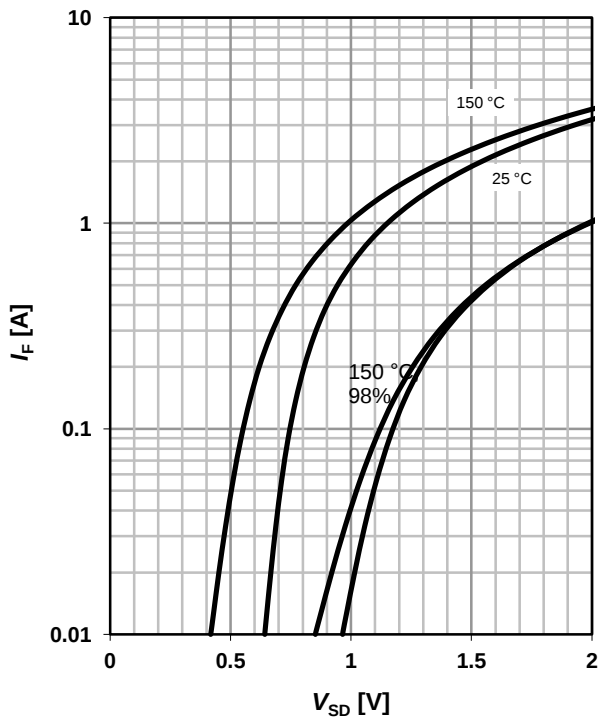
$$C = f(V_{DS}); V_{GS} = -3 \text{ V}; f = 1 \text{ MHz}$$



13 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

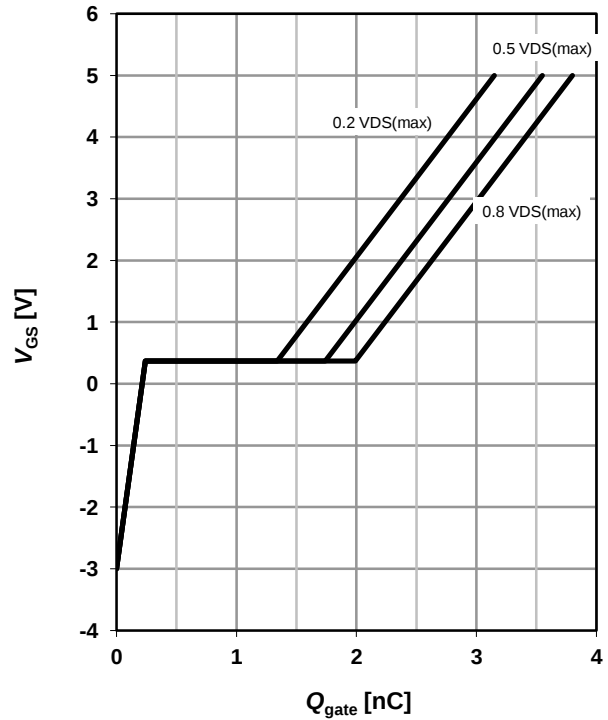
parameter: T_j



15 Typ. gate charge

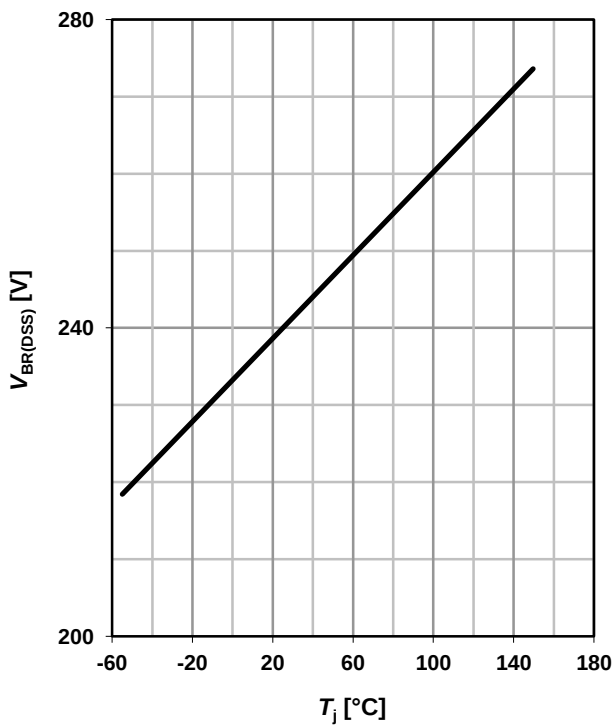
$$V_{GS} = f(Q_{gate}); I_D = 0.2 \text{ A pulsed}$$

parameter: V_{DD}

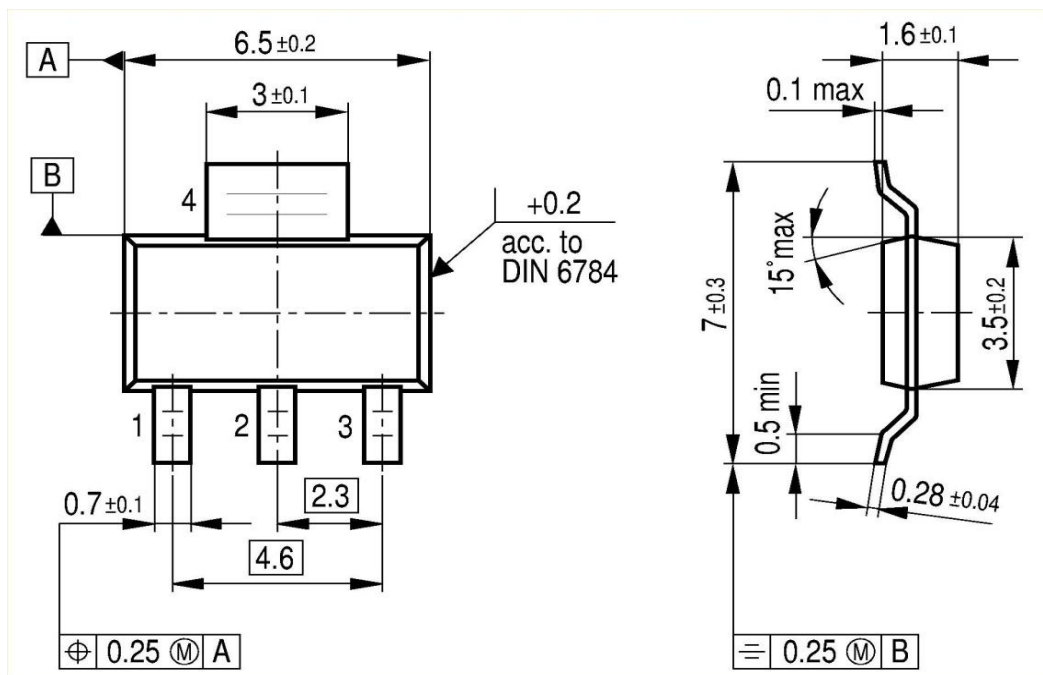


16 Drain-source breakdown voltage

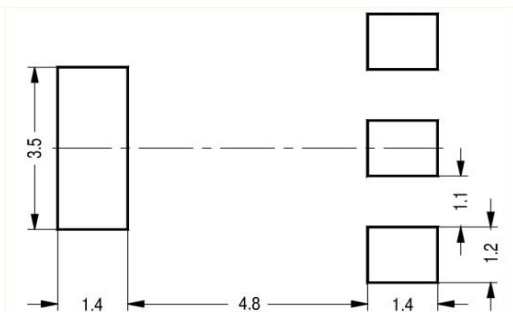
$$V_{BR(DSS)} = f(T_j); I_D = 250 \text{ } \mu\text{A}$$



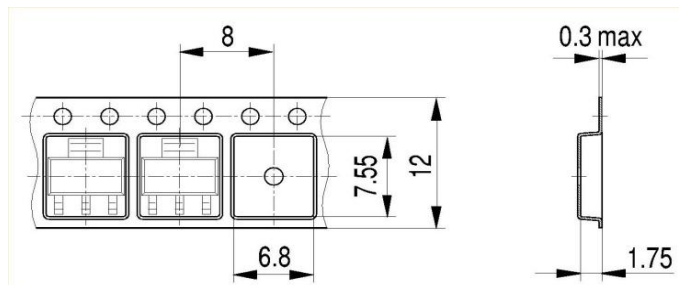
Package Outline:



Footprint:



Packaging:



Dimensions in mm

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